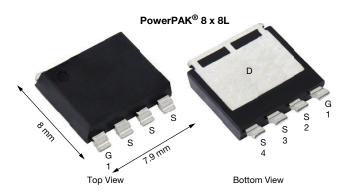
SQJQ160EL

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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

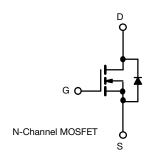


PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0011			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.00080			
I _D (A) ^e	461			
Configuration	Single			

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.6 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





0.43

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ160EL (for detailed order number please see <u>www.vishay.com/doc?79776</u>)

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unless	s otherwise noted	ł)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current ^e	T _C = 25 °C	۱ _D	461		
	T _C = 125 °C		266		
Continuous source current (diode conduction)	I _S	317	А		
Pulsed drain current ^a , e		I _{DM}	655		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	69		
Single pulse avalanche energy	L = 0.1 IIIH	E _{AS}	238	mJ	
Maximum power dissipation ^e	T _C = 25 °C	P _D	348	w	
	T _C = 125 °C		116		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	J°	
Soldering recommendations (peak temperatur		260	C		
THERMAL RESISTANCE RATING	ìS				
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^b	R _{thJA}	44	°C/W	

Junction-to-case (drain) d

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (www.vishay.com/doc?73257)

d. As per JESD51-14

e. Values based on RthJC and TC of 25 °C- Actual values achievable will be dependent on the thermal characteristics of the complete system

 R_{thJC}

1

°C/W

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	v
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	μA
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	500	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	А
Drain-source on-state resistance ^a		$V_{GS} = 4.5 V$	I _D = 20 A	-	0.00090	0.0011	- Ω
	Brach	$V_{GS} = 10 V$	I _D = 20 A	-	0.00056	0.00080	
	R _{DS(on)}	$V_{GS} = 10 V$	$I_D = 20 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.0014	52
		$V_{GS} = 10 V$	$I_D = 20 \text{ A}, \text{T}_\text{J} = 175 \ ^\circ\text{C}$	-	-	0.0017]
Forward transconductance b	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 40 \text{ A}$		-	205	-	S
Dynamic ^b							
Input capacitance	Ciss	V _{GS} = 0 V V _{DS}	V _{DS} = 25 V, f = 1 MHz	-	13 236	18 531	pF
Output capacitance	C _{oss}			-	4447	6226	
Reverse transfer capacitance	C _{rss}			-	219	307	
Total gate charge ^c	Qg		V _{DS} = 30 V, I _D = 50 A	-	206	309	nC
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V		-	42	-	
Gate-drain charge ^c	Q _{gd}			-	31	-	1
Gate resistance	Rg	f = 1 MHz		0.4	1.6	3.2	Ω
Turn-on delay time ^c	t _{d(on)}	$V_{DD}=30~V,~R_L=0.6~\Omega, \\ I_D\cong50~A,~V_{GEN}=10~V,~R_g=1~\Omega$		-	17	26	- ns
Rise time ^c	t _r			-	13	20	
Turn-off delay time ^c	t _{d(off)}			-	82	123	
Fall time ^c	t _f			-	20	30	
Source-Drain Diode Ratings and Charac	teristics ^b						
Pulsed current ^a	I _{SM}			-	-	655	Α
Forward voltage	V _{SD}	$I_{F} = 40 \text{ A}, V_{GS} = 0 \text{ V}$		-	0.7	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		-	86	172	ns
Body diode reverse recovery charge	Q _{rr}			-	174	348	nC
Reverse recovery fall time	ta			-	50	-	
Reverse recovery rise time	t _b			-	37	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			_	3.5	-	Α

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

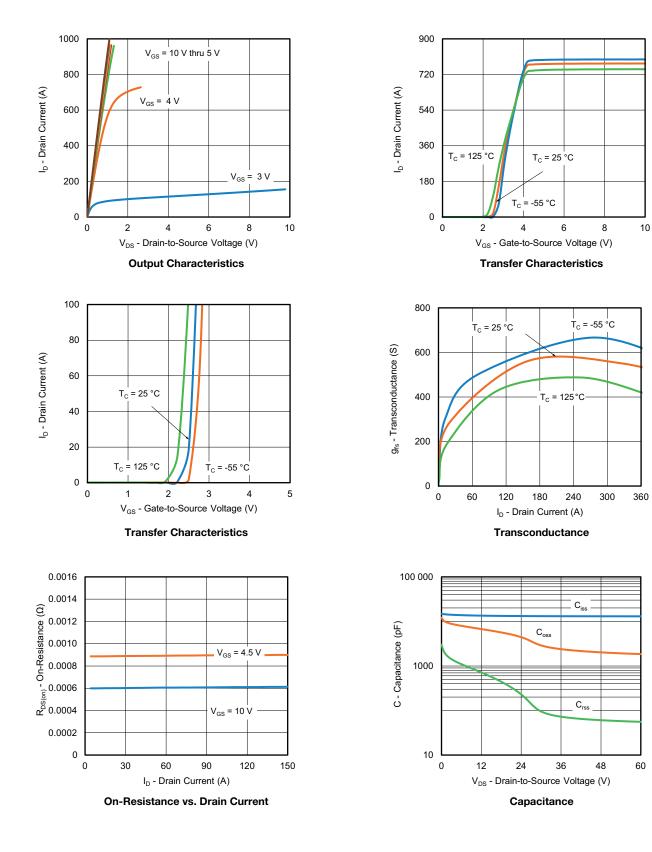
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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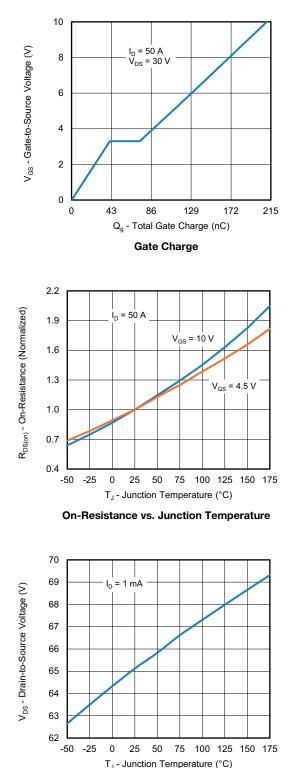
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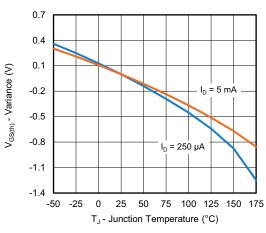


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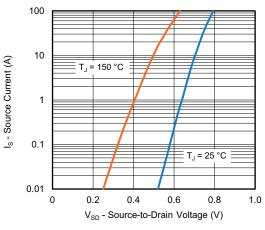
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



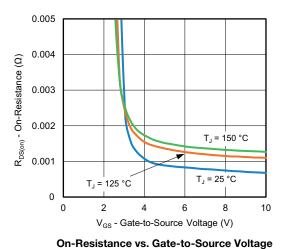
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage



Source Drain Diode Forward Voltage



Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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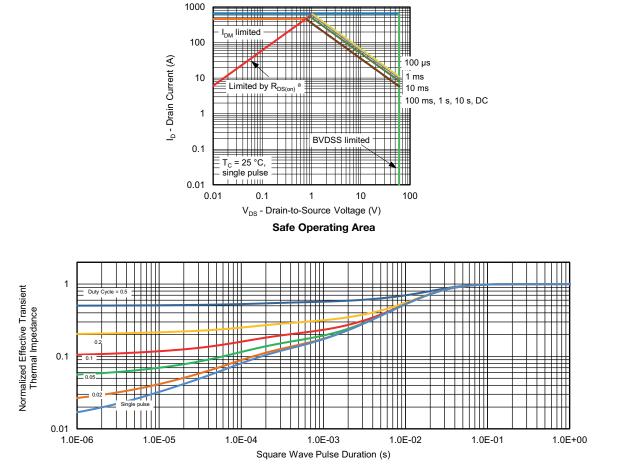
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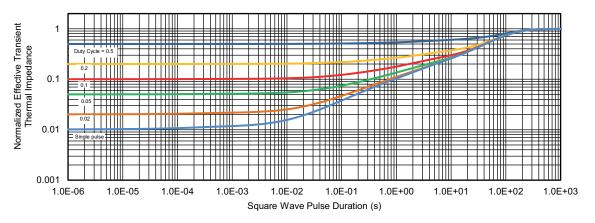
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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